

Application No. 09/943,094
Reply to Office Action of June 10, 2003
Amendment Dated September 9, 2003

Attorney Docket No. 81751.0017

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device, comprising:
a semiconductor substrate having a first conductive layer provided therein;
an insulation layer provided above the semiconductor substrate;
a semiconductor layer provided above the insulation layer, ~~wherein the semiconductor layer includes an element isolation region which has a connection hole;~~
a second conductive layer ~~provided above the semiconductor layer or~~ disposed in contact with the semiconductor layer, and electrically connected to the first conductive layer; and
a contact layer provided in ~~the~~ a first connection hole, the contact layer electrically connecting the first conductive layer and the second conductive layer.
2. (Original) The semiconductor device as defined by claim 1,
wherein the first conductive layer is formed from an impurity layer.
3. (Original) The semiconductor device as defined by claim 1,
wherein the first conductive layer functions as a wiring layer.
4. (Original) The semiconductor device as defined by claim 1,
wherein the first conductive layer functions as a resistance layer.

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5. (Currently Amended) The semiconductor device as defined by claim 1,
~~wherein a connection hole is provided for connecting the first conductive layer~~
~~to the second conductive layer, and~~
wherein the connection hole extends into the semiconductor substrate, ~~and~~
~~wherein a contact layer is provided in the connection hole.~~
6. (Original) The semiconductor device as defined by claim 1,
wherein a side wall is provided in the connection hole.
7. (Currently Amended) A semiconductor device, comprising:
a semiconductor substrate having a contact region provided therein;
an insulation layer provided above the semiconductor substrate; and
a semiconductor layer provided above the insulation layer, ~~wherein the~~
~~semiconductor layer includes an element isolation region which has a connection~~
~~hole;~~
a conductive layer ~~provided above the semiconductor layer or~~ disposed in
contact with the semiconductor layer, ~~and has a function of allowing~~ wherein the
conductive layer allows charge to flow into the semiconductor substrate, the contact
region being electrically connected to the conductive layer; and
a contact layer provided in the a first connection hole, the contact layer
electrically connecting the contact region and the conductive layer.
8. (Original) The semiconductor device as defined by claim 7,
wherein the contact region is formed from an impurity layer.

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9. (Original) The semiconductor device as defined by claim 7,
wherein a pn junction is formed by the contact region and the semiconductor substrate.
10. (Original) The semiconductor device as defined by claim 9,
wherein the semiconductor substrate is n-type, and
wherein the contact region is p-type.
11. (Original) The semiconductor device as defined by claim 9,
wherein the semiconductor substrate is p-type, and
wherein the contact region is n-type.
12. (Cancelled)
13. (Currently Amended) The semiconductor device as defined by claim ~~12~~ 7,
wherein a side wall is provided in the connection hole.

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14. (Currently Amended) A semiconductor device, comprising:
a semiconductor substrate having a first electrode provided therein;
an insulation layer provided above the semiconductor substrate;
a semiconductor layer provided above the insulation layer, the semiconductor layer having a second electrode provided therein, wherein the first electrode is connected electrically to a conductive layer disposed in contact with the semiconductor layer; and
wherein the first electrode, the second electrode, and the insulation layer [in cooperation turning] are configured as a capacitive element.
15. (Original) The semiconductor device as defined by claim 14,
wherein the first electrode is formed from a first impurity layer.
16. (Original) The semiconductor device as defined by claim 14,
wherein the second electrode is formed from a second impurity layer.
17. (Currently Amended) The semiconductor device as defined by claim 14,
wherein the first electrode is connected electrically to a conductive layer provided above the semiconductor layer ~~or in~~ the semiconductor layer.
18. (Original) The semiconductor device as defined by claim 17,
wherein a connection hole is provided for connecting the first electrode to the conductive layer, and
wherein a contact layer is provided in the connection hole.

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19. (Original) The semiconductor device as defined by claim 18,
wherein a side wall is provided in the connection hole.

20.-31. (Cancelled)

Please add the following new claims 32-44:

32. (New) The semiconductor device as defined by claim 1, wherein the first conductive layer is embedded in the semiconductor substrate.

33. (New) The semiconductor device as defined by claim 1, wherein the second conductive layer is formed independently of the contact layer.

34. (New) The semiconductor device as defined by claim 7, wherein the contact region is embedded in the semiconductor substrate.

35. (New) The semiconductor device as defined by claim 7, wherein the conductive layer is formed independently of the contact layer.

36. (New) The semiconductor device as defined by claim 14, wherein the first electrode is embedded in the semiconductor substrate.

37. (New) The semiconductor device as defined by claim 14, wherein the second electrode is formed independently of the contact layer.

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38. (New) The semiconductor device as defined by claim 1, wherein the semiconductor layer includes an element isolation region which has a second connection hole therein.

39. (New) The semiconductor device as defined by claim 1, wherein the second conductive layer provided above the semiconductor layer.

40. (New) The semiconductor device as defined by claim 1, wherein the second conductive layer provided in the semiconductor layer.

41. (New) The semiconductor device as defined by claim 7, wherein the semiconductor layer includes an element isolation region which has a second connection hole therein.

42. (New) The semiconductor device as defined by claim 7, wherein the conductive layer provided above the semiconductor layer.

43. (New) The semiconductor device as defined by claim 7, wherein the conductive layer provided in the semiconductor layer.

44. (New) The semiconductor device as defined by claim 14, wherein the first electrode is connected electrically to a conductive layer provided in the semiconductor layer.